



#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C		
001/	2Ω @ V <sub>GS</sub> = 4V	400mA		
60V	$2.5\Omega$ @ $V_{GS} = 2.5V$	350mA		

## **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Mechanical Data**

- Case: U-DFN1212-3 (Type C)
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 4
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)



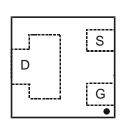




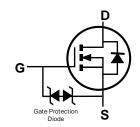
Top View



**Bottom View** 



Pin-Out Top View



Equivalent Circuit

## **Ordering Information** (Note 5)

Part Number	Compliance	Case	Packaging
DMN62D1LFDQ-7	Standard	U-DFN1212-3 (Type C)	3000/Tape & Reel
DMN62D1LFDQ-13	Standard	U-DFN1212-3 (Type C)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, see http://www.diodes.com/products/packages.html.

#### **Marking Information**



K63 YM

K64 = Product Type Marking Code K63 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Date Code	rtey												
Year	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	Α	В	С	D	Е	F	G	Н	1	J	K	L	М
Month	Jan	Feb	Mar	Apr	Ма	y J	un	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5		6	7	8	9	0	N	D



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	60	V	
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4V	Ι <sub>D</sub>	400 310	mA	
Pulsed Drain Current (Note 7)	I <sub>DM</sub>	1	А	

### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	0.5	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6)	R <sub>OJA</sub>	237	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

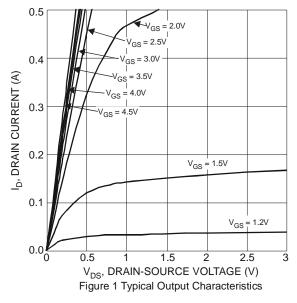
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA		
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V		
		_	_	±100	nA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±500	nA	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$		
		_	_	±2	μΑ	V <sub>GS</sub> = ±15V, V <sub>DS</sub> = 0V		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.6	_	1	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$		
		_	0.8	2		$V_{GS} = 4V, I_{D} = 100mA$		
Static Drain-Source On-Resistance	D	_	1	2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$ $V_{GS} = 1.8V, I_D = 50mA$		
Static Dialii-Source On-Resistance	R <sub>DS(ON)</sub>	_	1.4	3				
		_	1.8	_		$V_{GS} = 1.5V, I_D = 10mA$		
Forward Transfer Admittance	Y <sub>fs</sub>	_	1.8	_	S	$V_{DS} = 10V, I_D = 200mA$		
Diode Forward Voltage	V <sub>SD</sub>	_	8.0	1.3	V	$V_{GS} = 0V, I_{S} = 115mA$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	C <sub>iss</sub>		36			051/1/ 01/		
Output Capacitance	Coss	_	4.6	_	pF	$V_{DS} = 25V$ , $V_{GS} = 0V$ , f = 1MHz		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	3.6	_		1 - 11/11/12		
Gate Resistance	Rg	_	59.8	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$		
Total Gate Charge	Qg	_	0.55	_		45777		
Gate-Source Charge	Qgs	_	0.08	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250mA$		
Gate-Drain Charge	Q <sub>gd</sub>	_	0.12	_		ID = ZJUIIA		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	2.1	_	ns			
Turn-On Rise Time	t <sub>R</sub>	_	2.8	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	21	_	ns	$R_L = 150\Omega$ , $R_G = 25\Omega$ , $I_D = 200$ mA		
Turn-Off Fall Time	t <sub>F</sub>	_	13.9	_	ns	710 - 2001117		

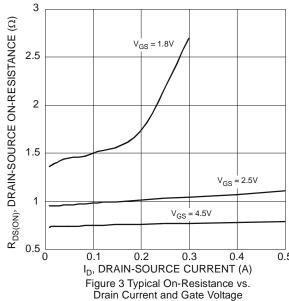
Notes:

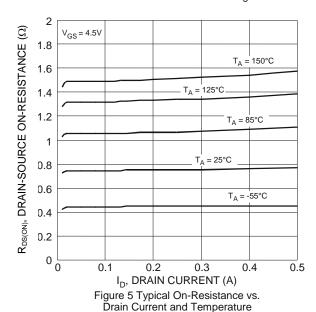
- 6. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
  7. Repetitive rating, pulse width limited by junction temperature.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to production testing.

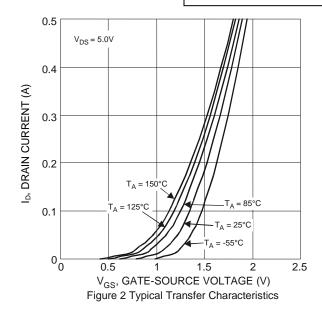


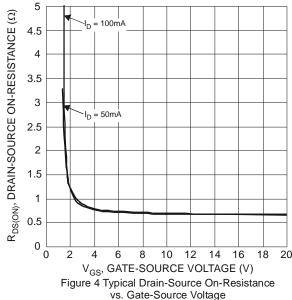


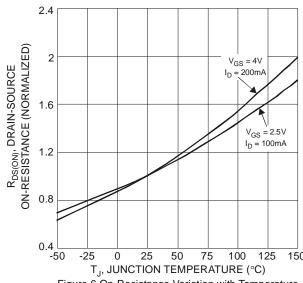






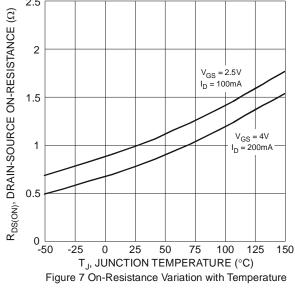


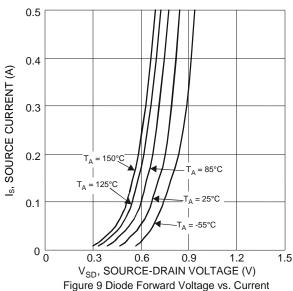


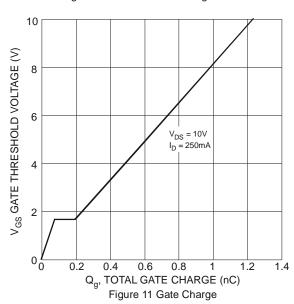


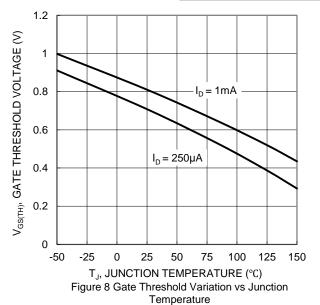


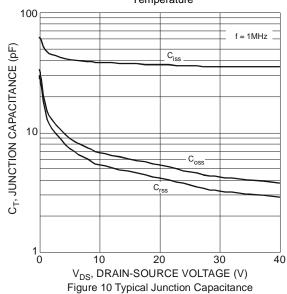


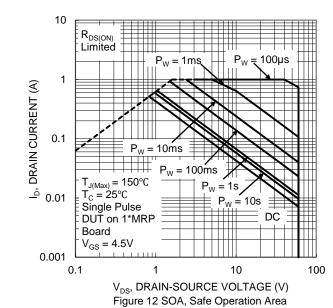




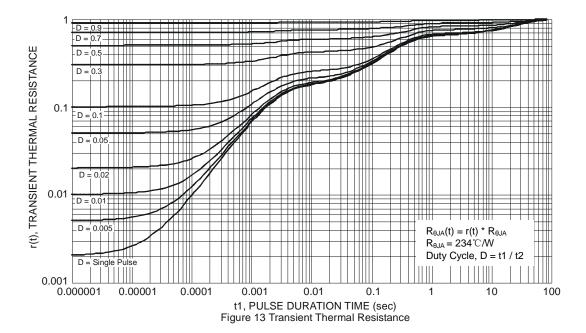








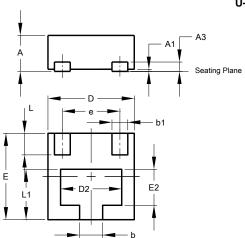






### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



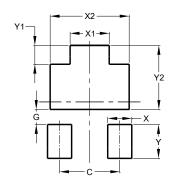
# U-DFN1212-3 (Type C)

U-DFN1212-3									
	Type C								
Dim	Min Max Typ								
Α	0.47	0.53	0.50						
A1	0	0.05	0.02						
A3	_	_	0.13						
b	0.27	0.37	0.32						
b1	0.17	0.27	0.22						
ם	1.15	1.25	1.20						
D2	0.75	0.95	0.85						
е	_	_	0.80						
Е	1.15	1.25	1.20						
E2	0.40	0.60	0.50						
L	0.25	0.35	0.30						
L1	0.65	0.75	0.70						
All Dimensions in mm									

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN1212-3 (Type C)



Dimensions	Value (in mm)
С	0.800
G	0.200
X	0.320
X1	0.520
X2	1.050
Υ	0.450
Y1	0.250
Y2	0.850



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2018, Diodes Incorporated

www.diodes.com